

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Inventors: Sheng Teng Hsu

Serial No: Not Yet Assigned

Filed: Herewith

Title: 3D CROSS-POINT MEMORY
ARRAY WITH SHARED
CONNECTIONS

PATENT APPLICATION

Attorney Docket No.
SLA0871

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

April 16, 2004
(Date)

Respectfully submitted,



Matthew D. Rabdau
Reg. No. 43,026

Matthew D. Rabdau, Patent Attorney
Sharp Laboratories of America, Inc.
5750 NW Pacific Rim Boulevard
Camas, WA 98607
Telephone: (360) 834-8567
Facsimile: (360) 817-8505

FORM PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION			DOCKET NUMBER SLA0871		APPLICATION NUMBER	
			APPLICANT Sheng Teng Hsu			
			FILING DATE: April 16, 2004		GROUP ART UNIT	

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILE. DATE IF APPROP.
	3,838,405	Sep., 1974	Arnett et al.			
	5,410,504	Apr., 1995	Ward.			
	5,508,953	Apr., 1996	Fukuda et al.			
	5,579,258	Nov., 1996	Adachi.			
	5,640,343	Jun., 1997	Gallagher et al.			
	5,712,612	Jan., 1998	Lee et al.			
	5,792,569	Aug., 1998	Sun et al.			
	5,991,193	Nov., 1999	Gallagher et al.			
	6,128,214	Oct., 2000	Kuekes et al.			
	6,198,208	Mar., 2001	Yano et al.			
	6,204,139	Mar., 2001	Liu et al.			
	6,473,332	Oct., 2002	Ignatiev et al.			
	6,479,848	Nov., 2002	Park et al.			
	6,569,745	May 2003	Hsu			

FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO

OTHER DOCUMENTS	
	Wu et al., "High Temperature Retention Properties of Ferroelectric PZT/YBCO Heterostructures Investigated by Pyroelectric Current and Phase Detection," 1996, Proceedings of the Tenth IEEE International Symposium on Applications of Ferroelectrics, p. 507-510.*
	Article entitled, "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", by S. Q. Liu et al., published in Applied Physics Letters, vol. 76, No. 19, May 8, 2000, pp 2749-2751.
	Article entitled, "Reproducible Switching Effect in Thin Oxide Films for Memory Applications", by A. Beck et al., published in Applied Physics Letters, vol. 77, No. 1, Jul. 3, 2000, pp. 139-141.

EXAMINER	DATE CONSIDERED
----------	-----------------